9DBU0931

DATASHEET

Description

The 9DBU0931 is a member of IDT's 1.5V Ultra-Low-Power (ULP) PCIe family. The device has 9 output enables for clock management, and 3 selectable SMBus addresses.

Recommended Application

1.5V PCIe Gen1-2-3 Fanout Buffer (FOB)

Output Features

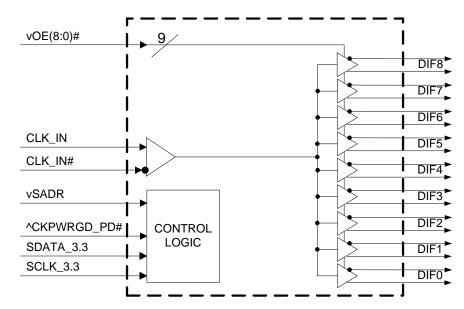
• 9 1–167MHz Low-Power (LP) HCSL DIF pairs

Key Specifications

- DIF additive cycle-to-cycle jitter < 5ps
- DIF output-to-output skew < 60ps
- DIF additive phase jitter is < 300fs rms for PCIe Gen 3
- DIF additive phase jitter < 350fs rms for SGMII

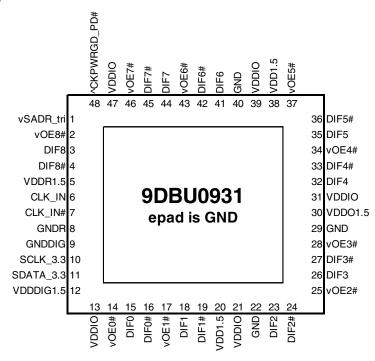
Features/Benefits

- LP-HCSL outputs; save 18 resistors compared to standard HCSL outputs
- 47mW typical power consumption in PLL mode; minimal power consumption
- Outputs can optionally be supplied from any voltage between 1.05 and 1.5V; maximum power savings
- Spread Spectrum (SS) compatible; allows SS for EMI reduction
- OE# pins for each output; support DIF power management
- HCSL-compatible differential input; can be driven by common clock sources
- SMBus-selectable features; optimize signal integrity to application
 - slew rate for each output
 - differential output amplitude
- Device contains default configuration; SMBus interface not required for device operation
- 3.3V tolerant SMBus interface works with legacy controllers
- Three selectable SMBus addresses; multiple devices can easily share an SMBus segment
- 6 × 6 mm 48-VFQFPN; minimal board space



Block Diagram

Pin Configuration



48-pin VFQFPN, 6x6 mm, 0.4mm pitch

^v prefix indicates internal 120KOhm pull up AND pull down resistor (biased to VDD/2)

v prefix indicates internal 120KOhm pull down resistor
 ^ prefix indicates internal 120KOhm pull up resistor

SMBus Address Selection Table

	SADR	Address	+ Read/Write bit
State of SADR on first application of	0	1101011	Х
CKPWRGD PD#	М	1101100	X
CKFWKGD_FD#	1	1101101	х

Power Management Table

CKPWRGD_PD#	CLK IN	SMBus	OEx# Pin	DIFx			
		OEx bit		True O/P	Comp. O/P		
0	Х	Х	Х	Low	Low		
1	Running	0	Х	Low	Low		
1	Running	1	0	Running	Running		
1	Running	1	1	Low	Low		

Power Connections

	Pin Number		Description
VDD	VDDIO GND		Description
			Input
5		8	receiver
			analog
12		9	Digital power
20,30,31,38	13,21,31,39,47	22,29,40	DIF outputs

Note: EPAD on this device is not electrically connected to the die. It should be connected to ground for best thermal performance.

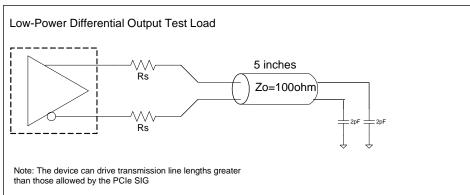
Pin Descriptions

PIN #	PIN NAME	TYPE	DESCRIPTION
1	vSADR tri	LATCHED	Tri-level latch to select SMBus Address. It has an internal 120kohm pull down
I		IN	resistor. See SMBus Address Selection Table.
2	vOE8#	IN	Active low input for enabling output 8. This pin has an internal 120kohm pull-
2	VOLO#		down.
3	DIF8	OUT	Differential true clock output.
4	DIF8#	OUT	Differential complementary clock output.
5	VDDR1.5	PWR	1.5V power for differential input clock (receiver). This VDD should be treated as
			an Analog power rail and filtered appropriately.
6	CLK_IN	IN	True input for differential reference clock.
7	CLK_IN#	IN	Complementary input for differential reference clock.
8	GNDR	GND	Analog ground pin for the differential input (receiver)
	GNDDIG	GND	Ground pin for digital circuitry.
	SCLK_3.3	IN	Clock pin of SMBus circuitry, 3.3V tolerant.
	SDATA_3.3	I/O	Data pin for SMBus circuitry, 3.3V tolerant.
12	VDDDIG1.5	PWR	1.5V digital power (dirty power)
13	VDDIO	PWR	Power supply for differential outputs
14	vOE0#	IN	Active low input for enabling output 0. This pin has an internal 120kohm pull- down.
15	DIF0	OUT	Differential true clock output.
16	DIF0#	OUT	Differential complementary clock output.
17	vOE1#	IN	Active low input for enabling output 1. This pin has an internal 120kohm pull- down.
18	DIF1	OUT	Differential true clock output.
	DIF1#	OUT	Differential complementary clock output.
20	VDD1.5	PWR	Power supply, nominally 1.5V
21	VDDIO	PWR	Power supply for differential outputs
22	GND	GND	Ground pin.
23	DIF2	OUT	Differential true clock output.
24	DIF2#	OUT	Differential complementary clock output.
25	vOE2#	IN	Active low input for enabling output 2. This pin has an internal 120kohm pull- down.
26	DIF3	OUT	Differential true clock output.
27	DIF3#	OUT	Differential complementary clock output.
	vOE3#	IN	Active low input for enabling output 3. This pin has an internal 120kohm pull- down.
29	GND	GND	Ground pin.
30	VDDO1.5	PWR	Power supply for outputs, nominally 1.5V.
31	VDDIO	PWR	Power supply for differential outputs
32	DIF4	OUT	Differential true clock output.
33	DIF4#	OUT	Differential complementary clock output.
	vOE4#	IN	Active low input for enabling output 4. This pin has an internal 120kohm pull- down.
35	DIF5	OUT	Differential true clock output.
	DIF5#	OUT	Differential complementary clock output.
	vOE5#	IN	Active low input for enabling output 5. This pin has an internal 120kohm pull- down.
38	VDD1.5	PWR	Power supply, nominally 1.5V
39	VDDIO	PWR	Power supply for differential outputs
40	GND	GND	Ground pin.
40			

Pin Descriptions (cont.)

PIN #	PIN NAME	TYPE	DESCRIPTION
41	DIF6	OUT	Differential true clock output.
42	DIF6#	OUT	Differential complementary clock output.
43	vOE6#	IN	Active low input for enabling output 6. This pin has an internal 120kohm pull- down.
44	DIF7	OUT	Differential true clock output.
45	DIF7#	OUT	Differential complementary clock output.
46	vOE7#	IN	Active low input for enabling output 7. This pin has an internal 120kohm pull- down.
47	VDDIO	PWR	Power supply for differential outputs
48	^CKPWRGD_PD#	IN	Input notifies device to sample latched inputs and start up on first high assertion. Low enters Power Down Mode, subsequent high assertions exit Power Down Mode. This pin has internal 120kohm pull-up resistor.
49	EPAD	GND	Connect EPAD to ground.

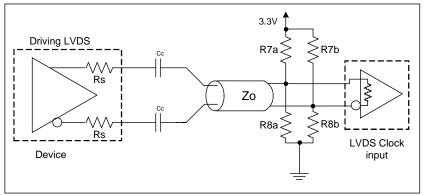
Test Loads



Alternate Differential Output Terminations

-	Rs	Zo	Units
ſ	33	100	Ohms
	27	85	Onins

Driving LVDS



Driving LVDS inputs

	\ \		
Component	Receiver has termination	er has Receiver does not ation have termination	
R7a, R7b	10K ohm	140 ohm	
R8a, R8b	5.6K ohm	75 ohm	
Cc	0.1µF	0.1µF	
Vcm	1.2 volts	1.2 volts	

Absolute Maximum Ratings

Stresses above the ratings listed below can cause permanent damage to the 9DBU0931. These ratings, which are standard values for IDT commercially rated parts, are stress ratings only. Functional operation of the device at these or any other conditions above those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods can affect product reliability. Electrical parameters are guaranteed only over the recommended operating temperature range.

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS	NOTES
Supply Voltage	VDDx	Applies to VDD, VDDA and VDDIO	-0.5		2	V	1,2
Input Voltage	V _{IN}		-0.5		V _{DD} +0.5	V	1,
Input High Voltage, SMBus	VIHSMB	SMBus clock and data pins			3.3	V	1
Storage Temperature	Ts		-65		150	°C	1
Junction Temperature	Tj				125	°C	1
Input ESD Protection	ESD prot	Human Body Model	2000			V	1

¹Guaranteed by design and characterization, not 100% tested in production.

² Operation under these conditions is neither implied nor guaranteed.

³ Not to exceed 2.0V.

Electrical Characteristics–Clock Input Parameters

 $TA = T_{AMB}$, Supply voltages per normal operation conditions; see Test Loads for loading conditions

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS	NOTES
Input Common Mode Voltage - DIF_IN	V _{COM}	Common mode input voltage	200		725	mV	1
Input Swing - DIF_IN	V _{SWING}	Differential value	300		1450	mV	1
Input Slew Rate - DIF_IN	dv/dt	Measured differentially	0.4		8	V/ns	1,2
Input Leakage Current	I _{IN}	$V_{IN} = V_{DD}, V_{IN} = GND$	-5		5	μA	
Input Duty Cycle	d _{tin}	Measurement from differential waveform	45	50	55	%	1
Input Jitter - Cycle to Cycle	J _{DIFIn}	Differential measurement	0		150	ps	1

¹ Guaranteed by design and characterization, not 100% tested in production.

² Slew rate measured through +/-75mV window centered around differential zero.

Electrical Characteristics–Input/Supply/Common Parameters–Normal Operating Conditions

 $TA = T_{AMB}$, Supply voltages per normal operation conditions; see Test Loads for loading conditions

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	МАХ	UNITS	NOTES
Supply Voltage	VDDx	Supply voltage for core and analog	1.425	1.5	1.575	V	
Output Supply Voltage	VDDIO	Low voltage supply LP-HCSL outputs	0.95	1.05-1.5	1.575	V	
Ambient Operating	T _{AMB}	Commercial range	0	25	70	°C	1
Temperature	AMB	Industrial range	-40	25	85	°C	1
Input High Voltage	V _{IH}	Single-ended inputs, except SMBus	$0.75 V_{DD}$		$V_{DD} + 0.3$	V	
Input Mid Voltage	VIM	Single-ended tri-level inputs ('_tri' suffix)	$0.4 V_{DD}$		$0.6 V_{DD}$	V	
Input Low Voltage	V _{IL}	Single-ended inputs, except SMBus	-0.3		$0.25 V_{DD}$	V	
	I _{IN}	Single-ended inputs, $V_{IN} = GND$, $V_{IN} = VDD$	-5		5	μA	
Input Current		Single-ended inputs					
input outoint	I _{INP}	$V_{IN} = 0 V$; inputs with internal pull-up resistors	-200		200	μA	
		$V_{IN} = VDD$; inputs with internal pull-down resistors					
Input Frequency	F _{in}		1		167	MHz	2
Pin Inductance	L _{pin}				7	nH	1
	CIN	Logic Inputs, except DIF_IN	1.5		5	pF	1
Capacitance	C _{INDIF_IN}	DIF_IN differential clock inputs	1.5		2.7	pF	1,5
	C _{OUT}	Output pin capacitance			6	pF	1
Clk Stabilization	T _{STAB}	From V _{DD} Power-Up and after input clock stabilization or de-assertion of PD# to 1st clock			1	ms	1,2
Input SS Modulation Frequency PCIe	f _{MODINPCIe}	Allowable Frequency for PCIe Applications (Triangular modulation)	30		33	kHz	
Input SS Modulation Frequency non-PCIe	f _{MODIN}	Allowable Frequency for non-PCIe Applications (Triangular modulation)	0		66	kHz	
OE# Latency	t _{LATOE#}	DIF start after OE# assertion DIF stop after OE# deassertion	1		3	clocks	1,3
Tdrive_PD#	t _{DRVPD}	DIF output enable after PD# de-assertion			300	μs	1,3
Tfall	t _F	Fall time of single-ended control inputs			5	ns	2
Trise	t _R	Rise time of single-ended control inputs			5	ns	2
SMBus Input Low Voltage	VILSMB				0.6	V	
SMBus Input High Voltage	VIHSMB	$V_{DDSMB} = 3.3V$, see note 4 for $V_{DDSMB} < 3.3V$	2.1		3.3	V	4
SMBus Output Low Voltage	V _{OLSMB}	at I _{PULLUP}			0.4	V	
SMBus Sink Current	IPULLUP	at V _{OL}	4			mA	1
Nominal Bus Voltage	V _{DDSMB}	Bus Voltage	1.425		3.3	V	
SCLK/SDATA Rise Time	t _{RSMB}	(Max VIL - 0.15V) to (Min VIH + 0.15V)			1000	ns	1
SCLK/SDATA Fall Time	t _{FSMB}	(Min VIH + 0.15V) to (Max VIL - 0.15V)			300	ns	1
SMBus Operating Frequency	f _{MAXSMB}	Maximum SMBus operating frequency			400	kHz	6

¹ Guaranteed by design and characterization, not 100% tested in production.

² Control input must be monotonic from 20% to 80% of input swing.

 3 Time from deassertion until outputs are > 200 mV.

 4 For V_{DDSMB} < 3.3V, V_{IHSMB} > = 0.8xV_{DDSMB}

⁵ DIF_IN input.

⁶ The differential input clock must be running for the SMBus to be active.

Electrical Characteristics–DIF Low-Power HCSL Outputs

TA = T_{AMB}, Supply voltages per normal operation conditions; see Test Loads for loading conditions

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS	NOTES
Slew rate	dV/dt	Scope averaging on, fast setting	1.4	2.3	3.5	V/ns	1,2,3
Siew late	dV/dt	Scope averaging on, slow setting	0.9	1.5	2.5	V/ns	1,2,3
Slew rate matching	∆dV/dt	Slew rate matching, scope averaging on		9.3	20	%	1,2,4
Voltage High	V _{HIGH}	Statistical measurement on single-ended signal	630	750	850	mV	7
Voltage Low	V _{LOW}	using oscilloscope math function. (Scope averaging on)		26	150		7
Max Voltage	Vmax	Measurement on single ended signal using		763	1150	mV	7
Min Voltage	Vmin	absolute value. (Scope averaging off)	-300	22		mv	7
Vswing	Vswing	Scope averaging off	300	1448		mV	1,2
Crossing Voltage (abs)	Vcross_abs	Scope averaging off	250	390	550	mV	1,5
Crossing Voltage (var)	∆-Vcross	Scope averaging off		11	140	mV	1,6

¹Guaranteed by design and characterization, not 100% tested in production.

² Measured from differential waveform.

³ Slew rate is measured through the Vswing voltage range centered around differential 0V. This results in a +/-150mV window around differential 0V.

⁴ Matching applies to rising edge rate for Clock and falling edge rate for Clock#. It is measured using a +/-75mV window centered on the average cross point where Clock rising meets Clock# falling. The median cross point is used to calculate the voltage thresholds the oscilloscope is to use for the edge rate calculations.

⁵ Vcross is defined as voltage where Clock = Clock# measured on a component test board and only applies to the differential rising edge (i.e. Clock rising and Clock# falling).

⁶ The total variation of all Vcross measurements in any particular system. Note that this is a subset of Vcross_min/max (Vcross absolute) allowed. The intent is to limit Vcross induced modulation by setting Δ -Vcross to be smaller than Vcross absolute.

⁷ At default SMBus settings.

Electrical Characteristics–Current Consumption

 $TA = T_{AMB}$, Supply voltages per normal operation conditions; see Test Loads for loading conditions

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS	NOTES
Operating Supply Current	I _{DDA}	VDDO1.5+VDDR, PLL Mode, at 100MHz		2.2	3	mA	
	I _{DD}	VDDx, All outputs active at 100MHz		4	6	mA	
	I _{DDIO}	VDDIO, All outputs active at 100MHz		35	40	mA	
	I _{DDAPD}	VDDO1.5+VDDR, CKPWRGD_PD#=0		0.4	1	mA	2
Powerdown Current	I _{DDPD}	VDDx, CKPWRGD_PD#=0		0.2	0.6	mA	2
	IDDIOPD	VDDIO, CKPWRGD_PD#=0		0.0004	0.1	mA	2

¹ Guaranteed by design and characterization, not 100% tested in production.

² Input clock stopped.

Electrical Characteristics–Output Duty Cycle, Jitter, Skew and PLL Characteristics

 $TA = T_{AMB}$, Supply voltages per normal operation conditions; see Test Loads for loading conditions

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS	NOTES
Duty Cycle Distortion	t _{DCD}	Measured differentially, at 100MHz	-1	-0.2	0.5	%	1,3
Skew, Input to Output	t _{pdBYP}	V _T = 50%	2400	2862	3700	ps	1
Skew, Output to Output	t _{sk3}	V _T = 50%		30	60	ps	1,4
Jitter, Cycle to Cycle	t _{jcyc-cyc}	Additive Jitter		0.1	5	ps	1,2

¹ Guaranteed by design and characterization, not 100% tested in production.

² Measured from differential waveform.

³ Duty cycle distortion is the difference in duty cycle between the output and the input clock.

⁴ All outputs at default slew rate.

Electrical Characteristics–Phase Jitter Parameters

TA = T_{AMB}. Supply voltages per normal operation conditions; see Test Loads for loading conditions

						INDUSTRY		
PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	LIMIT	UNITS	Notes
	t _{jphPCleG1}	PCIe Gen 1		0.1	5	N/A	ps (p-p)	1,2,3,5
	+	PCIe Gen 2 Low Band 10kHz < f < 1.5MHz		0.1	0.4	N/A	ps (rms)	1,2,3,4, 5
	t _{jphPCleG2}	PCIe Gen 2 High Band 1.5MHz < f < Nyquist (50MHz)		0.1	0.7	N/A	ps (rms)	1,2,3,4
Additive Phase Jitter	t _{jphPCleG3}	PCIe Gen 3 (2-4MHz or 2-5MHz, CDR = 10MHz)		0.1	0.3	N/A	ps (rms)	1,2,3,4
	t _{jphSGMIIM0}	125MHz, 1.5MHz to 10MHz, -20dB/decade rollover < 1.5MHz, -40db/decade rolloff > 10MHz		200	250	N/A	fs (rms)	1,6
	t _{jphSGMIIM1}	125MHz, 12kHz to 20MHz, -20dB/decade rollover < 1.5MHz, -40db/decade rolloff > 10MHz		313	350	N/A	fs (rms)	1,6

¹Guaranteed by design and characterization, not 100% tested in production.

² See http://www.pcisig.com for complete specs.

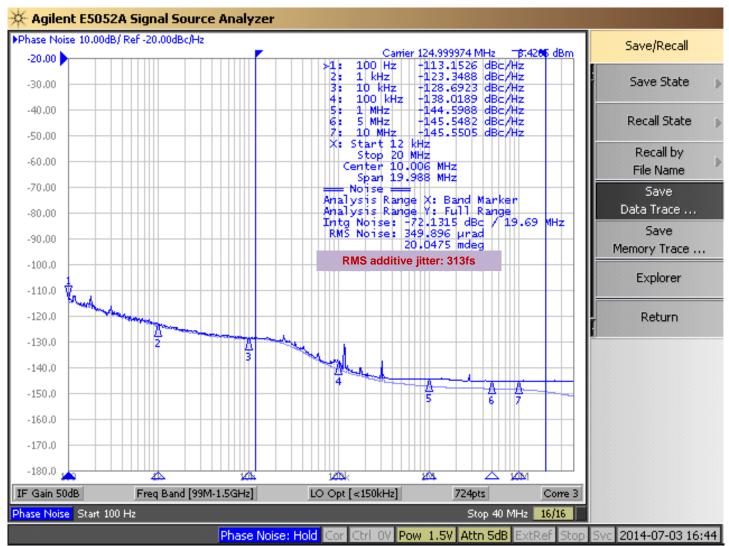
³ Sample size of at least 100K cycles. This figure extrapolates to 108ps pk-pk @ 1M cycles for a BER of 1-12.

⁴ For RMS figures, additive jitter is calculated by solving the following equation: Additive jitter = SQRT[(total jitter)² - (input jitter)²].

⁵ Driven by 9FGV0831 or equivalent.

⁶ Rohde & Schwarz SMA100.

Additive Phase Jitter Plot: 125M (12kHz to 20MHz)



General SMBus Serial Interface Information

How to Write

- Controller (host) sends a start bit
- Controller (host) sends the write address
- IDT clock will acknowledge
- Controller (host) sends the beginning byte location = N
- IDT clock will **acknowledge**
- Controller (host) sends the byte count = X
- IDT clock will **acknowledge**
- Controller (host) starts sending Byte N through Byte N+X-1
- IDT clock will acknowledge each byte one at a time
- Controller (host) sends a stop bit

	Index Bl	ock V	Vrite Operation
Controll	er (Host)		IDT (Slave/Receiver)
Т	starT bit		
Slave A	Address		
WR	WRite		
			ACK
Beginning	g Byte = N		
			ACK
Data Byte	Count = X		
			ACK
Beginnir	ng Byte N		
			ACK
0		×	
0		X Byte	0
0		Ð	0
			0
Byte N	+ X - 1		
			ACK
Р	stoP bit		

Note: SMBus Address is Latched on SADR pin.

How to Read

- Controller (host) will send a start bit
- Controller (host) sends the write address
- IDT clock will acknowledge
- Controller (host) sends the beginning byte location = N
- IDT clock will acknowledge
- Controller (host) will send a separate start bit
- Controller (host) sends the read address
- IDT clock will acknowledge
- IDT clock will send the data byte count = X
- IDT clock sends Byte N+X-1
- IDT clock sends Byte 0 through Byte X (if X_(H) was written to Byte 8)
- Controller (host) will need to acknowledge each byte
- Controller (host) will send a not acknowledge bit
- Controller (host) will send a stop bit

	Index Block F	lead O	peration
Cor	ntroller (Host)		IDT (Slave/Receiver)
Т	starT bit		
SI	ave Address		
WR	WRite	-	
		-	ACK
Begi	nning Byte = N		
		-	ACK
RT	Repeat starT	-	
SI	ave Address		
RD	ReaD		
			ACK
			Data Byte Count=X
	ACK		
		-	Beginning Byte N
	ACK		
		e	0
	0	X Byte	0
	0	×	0
	0		
			Byte N + X - 1
Ν	Not acknowledge		
Р	stoP bit		

Byte 0	Name	Control Function	Туре	0	1	Default
Bit 7	DIF OE7	Output Enable	RW	Low/Low	Enabled	1
Bit 6	DIF OE6	Output Enable	RW	Low/Low	Enabled	1
Bit 5	DIF OE5	Output Enable	RW	Low/Low	Enabled	1
Bit 4	DIF OE4	Output Enable	RW	Low/Low	Enabled	1
Bit 3	DIF OE3	Output Enable	RW	Low/Low	Enabled	1
Bit 2	DIF OE2	Output Enable	RW	Low/Low	Enabled	1
Bit 1	DIF OE1	Output Enable	RW	Low/Low	Enabled	1
Bit 0	DIF OE0	Output Enable	RW	Low/Low	Enabled	1

SMBus Table: Output Enable Register ¹

1. A low on these bits will override the OE# pin and force the differential output Low/Low

SMBus Table: Output Enable and Output Amplitude Control Register

Byte 1	Name	Control Function	Туре	0	1	Default
Bit 7	Reserved					
Bit 6	Reserved					1
Bit 5	DIF OE8	DIF OE8 Output Enable RW Low/Low Enabled				1
Bit 4	Reserved					
Bit 3		Reserved				1
Bit 2		Reserved				1
Bit 1	AMPLITUDE 1	Controls Output Amplitude	RW	00 = 0.55V	01= 0.65V	1
Bit 0	AMPLITUDE 0		RW	10 = 0.7V	11 = 0.8V	0

1. A low on the DIF OE bit will override the OE# pin and force the differential output Low/Low

SMBus Table: DIF Slew Rate Control Register

Byte 2	Name	Control Function	Туре	0	1	Default
Bit 7	SLEWRATESEL DIF7	Adjust Slew Rate of DIF7	RW	Slow Setting	Fast Setting	1
Bit 6	SLEWRATESEL DIF6	Adjust Slew Rate of DIF6	RW	Slow Setting	Fast Setting	1
Bit 5	SLEWRATESEL DIF5	Adjust Slew Rate of DIF5	RW	Slow Setting	Fast Setting	1
Bit 4	SLEWRATESEL DIF4	Adjust Slew Rate of DIF4	RW	Slow Setting	Fast Setting	1
Bit 3	SLEWRATESEL DIF3	Adjust Slew Rate of DIF3	RW	Slow Setting	Fast Setting	1
Bit 2	SLEWRATESEL DIF2	Adjust Slew Rate of DIF2	RW	Slow Setting	Fast Setting	1
Bit 1	SLEWRATESEL DIF1	Adjust Slew Rate of DIF1	RW	Slow Setting	Fast Setting	1
Bit 0	SLEWRATESEL DIF0	Adjust Slew Rate of DIF0	RW	Slow Setting	Fast Setting	1

Note: See "DIF 0.7V Low-Power HCSL Outputs" table for slew rates.

SMBus Table: DIF Slew Rate Control Register

Byte 3	Name	Control Function	Туре	0	1	Default
Bit 7		Reserved				1
Bit 6		Reserved				1
Bit 5		Reserved				0
Bit 4	Reserved					
Bit 3		Reserved				0
Bit 2		Reserved				1
Bit 1	Reserved					1
Bit 0	SLEWRATESEL DIF8	Adjust Slew Rate of DIF8	RW	Slow Setting	Fast Setting	1
		, I. Outmutall table for eleve note		9	5	1

Note: See "DIF 0.7V Low-Power HCSL Outputs" table for slew rates.

Byte 4 is Reserved and reads back 'hFF

RENESAS

SMBus Table: Revision and Vendor ID Register

Byte 5	Name	Control Function	Туре	0	1	Default
Bit 7	RID3		R			0
Bit 6	RID2	Revision ID	R	A rov-	A rev = 0000	
Bit 5	RID1	Revision ID	R	A 160 -	0	
Bit 4	RID0		R		0	
Bit 3	VID3		R			0
Bit 2	VID2	VENDOR ID	R	0001		0
Bit 1	VID1		R	0001 = IDT		0
Bit 0	VID0		R			1

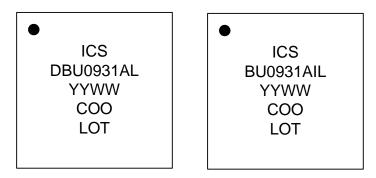
SMBus Table: Device Type/Device ID

Byte 6	Name	Control Function	Туре	0	1	Default
Bit 7	Device Type1	Device Type	R	00 = FGx,	01 = DBx,	1
Bit 6	Device Type0	Device туре	R	10 = DMx, 11=	1	
Bit 5	Device ID5		R			0
Bit 4	Device ID4		R			0
Bit 3	Device ID3	Device ID	R	001001 bina	ny or 00 bey	1
Bit 2	Device ID2	Device ID	R	001001 011a	001 binary or 09 hex	
Bit 1	Device ID1		R]		0
Bit 0	Device ID0]	R			1

SMBus Table: Byte Count Register

Byte 7	Name	Control Function	Туре	0	1	Default	
Bit 7	Reserved						
Bit 6	Reserved						
Bit 5	Reserved						
Bit 4	BC4		RW			0	
Bit 3	BC3		RW	Writing to this regist	er will configure how	1	
Bit 2	BC2	Byte Count Programming	RW	many bytes will be r	ead back, default is	0	
Bit 1	BC1		RW	= 8 b	ytes.	0	
Bit 0	BC0		RW			0	

Marking Diagrams



Notes:

- 1. "LOT" is the lot sequence number.
- 2. "COO" denotes country of origin.
- 3. YYWW is the last two digits of the year and week that the part was assembled.
- 4. Line 2: truncated part number
- 5. "L" denotes RoHS compliant package.
- 6. "I" denotes industrial temperature range device.

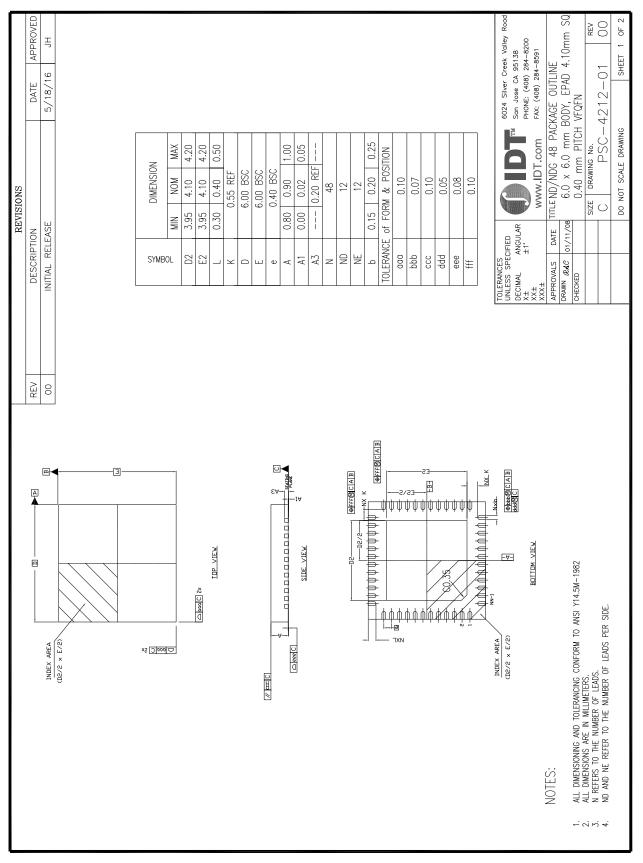
Thermal Characteristics

PARAMETER	SYMBOL	CONDITIONS	PKG	TYP VALUE	UNITS	NOTES
	θ _{JC}	Junction to Case		33	°C/W	1
	θ_{Jb}	Junction to Base	NDG48 2.1 37 30 27		°C/W	1
Thermal Resistance	θ _{JΑ0θ}	Junction to Air, still air			°C/W	1
mermai nesistance	θ_{JA1}	Junction to Air, 1 m/s air flow			°C/W	1
	θ_{JA3}	Junction to Air, 3 m/s air flow			°C/W	1
	θ_{JA5}	Junction to Air, 5 m/s air flow		26	°C/W	1

¹ePad soldered to board

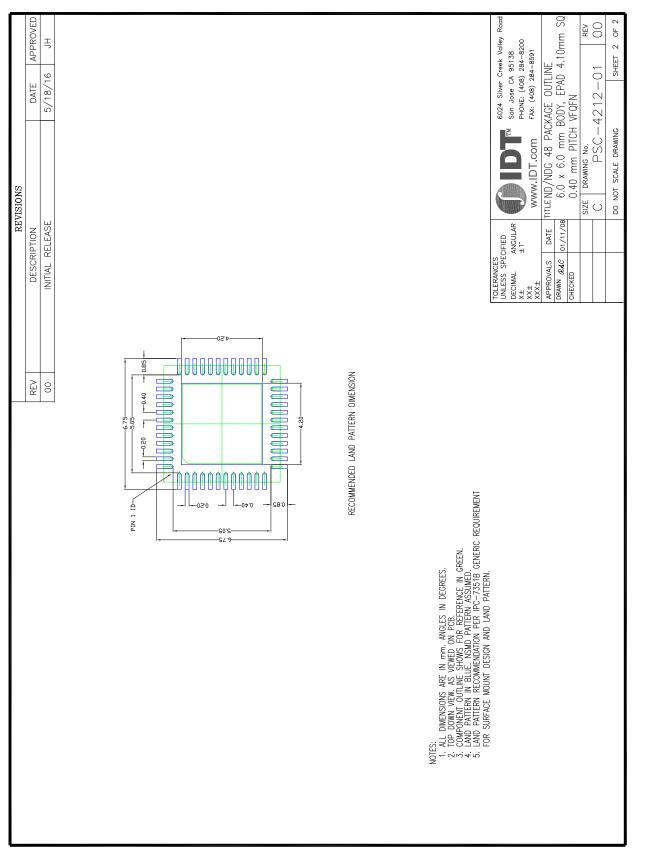
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Package Outline and Dimensions (NDG48)



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Package Outline and Dimensions (NDG48), cont.



Ordering Information

Part / Order Number	Shipping Packaging	Package	Temperature	
9DBU0931AKLF	Trays	48-pin VFQFPN	0 to +70° C	
9DBU0931AKLFT	Tape and Reel	48-pin VFQFPN	0 to +70° C	
9DBU0931AKILF	Trays	48-pin VFQFPN	-40 to +85° C	
9DBU0931AKILFT	Tape and Reel	48-pin VFQFPN	-40 to +85° C	

"LF" suffix to the part number are the Pb-Free configuration and are RoHS compliant. "A" is the device revision designator (will not correlate with the datasheet revision).

Revision History

Rev.	Initiator	Issue Date	Description	Page #
Α	RDW	7/16/2014	1. Updated electrical tables with final parameters.	
В	RDW	9/19/2014	Updated SMBus Input High/Low parameters conditions, MAX values, and footnotes.	
с	RDW	4/22/2015	 Updated pin out and pin descriptions to show ePad on package connected to ground. Minor updates to front page text for family consistency. Updated Clock Input Parameters table to be consistent with PCIe Vswing parameter. 	1-5
D	RDW	2/16/2017	1. Updated pins 30 and 29 from VDDA1.5 and GNDA to VDDO1.5 and GND to clearly indicate that this part has no PLL.	
E	RDW	3/9/2017	 Removed "Bypass Mode" reference in "Output Duty Cycle" and "Phase Jitter Parameters" tables; update note 3 under Output Duty Cycle table. Corrected spelling errors/typos. Change VDDA to VDDO1.5 in Current Consumption table. Update Additive Phase Jitter conditions for PCIe Gen3. 	



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